NAME	IC31	
LAYOUT (20:1 SCALE)		
EXPERIMENT	PHENIX	
SUB-DETECTOR	TIME EXPANSION CHAMBER TRACKER (TEC)	
C <sub>DET</sub> RANGE	10 - 40 PF	
CIRCUIT	CALIBRATION, PREAMP, DUAL-GAIN SHAPER, TAIL CANCELLATION	
NO. CHANNELS	8 DATA + 1 COMMON-MODE SENSE	
CHIP SIZE	3.35MM X 4.90MM	
PACKAGE	68-PIN CERAMIC J-LEADED CHIP CARRIER	
GAIN	LOW GAIN OUTPUT: 2 - 6 MV/FC, PROGRAMMABLE IN 8 STEPS HIGH GAIN OUTPUT: 9 - 31 MV/FC, "	
PULSE SHAPE	UNIPOLAR SEMIGAUSSIAN, 65 - 95 NSEC PEAKING TIME, PROGRAMMABLE IN 4 STEPS, ION TAIL CANCELLATION	
SIGNAL	1FC - 1PC	
NOISE	1500 ELECTRONS R.M.S.	
POWER	40 MW/CHANNEL	
COMMENT	1ST LOT YIELD 321/324 CHANNELS; SIGMA(GAIN) ~ 2.2%	

NAME	IC34		
LAYOUT (20:1 SCALE)			
EXPERIMENT	ATLAS		
SUB-DETECTOR	CATHODE STRIP CHAMBER (MUON ENDCAP)		
C <sub>DET</sub> RANGE	40 - 150 PF		
CIRCUIT	CALIBRATION, AMPLITIDE (PREAMP/SHAPER, TRACK+HOLD, MUX), TIM- ING(CONSTANT FRACTION DISCRIMINATOR)		
NO. CHANNELS	8		
CHIP SIZE	4.75MM X 5.29MM		
PACKAGE	84-PIN CERAMIC J-LEADED CHIP CARRIER		
GAIN	5 - 20 MV/FC, PROGRAMMABLE IN 4 STEPS		
PULSE SHAPE	BIPOLAR SEMIGAUSSIAN WITH 130 - 550 NSEC PEAKING TIME, PROGRAM- MABLE IN 4 STEPS		
SIGNAL	TO 250 FC		
NOISE	1800 ELECTRONS R.M.S. (WITH FASTEST SHAPING, C <sub>DET</sub> = 65 PF)		
POWER	70 MW/CHANNEL		
COMMENT	FACILITATES DATA-DRIVEN READOUT ARCHITECTURE (NO ANALOG PIPE- LINE)		

NAME	IC35	IC37
LAYOUT (20:1 SCALE)		
EXPERIMENT	STAR	
SUB-DETECTOR	SILICON VERTEX TRACKER (DRIFT DET.)	
C <sub>DET</sub> RANGE	0.8 PF	
CIRCUIT	CALIBRATION, PREAMP, SHAPER	
NO. CHANNELS	16	
CHIP SIZE	2.65MM X 4.33 MM	2.26MM X 3.11MM
PACKAGE	DIRECT WIREBONDING TO HYBRID SUBSTRATE	
GAIN	33 MV/FC	20 - 90 MV/FC, IN 4 STEPS
PULSE SHAPE	UNIPOLAR SEMIGAUSSIAN, 50 NSEC PEAKING	
SNR	120:1	
POWER	11 MW/CHANNEL	6.5 MW/CHANNEL
COMMENT	5 MW STABLE, LINEAR MOS RESISTOR FOR LOW PARALLEL NOISE IC37 HAS DC SENSE OF DETECTOR LEAKAGE, "HIGH DRIVE" MODE TO DRIVE 2M CABLE	

Fig. 2







a) ENC vs. peaking time (using external shaper).

b) Preamp and preamp/shaper output for varying VG.

c) Preamp/shaper output for varying temperature.

e) Am<sup>241</sup> spectrum, measured using 1 pF Si detector, CMOS preamp + external shaper, room temperature